SESDU5V0WB



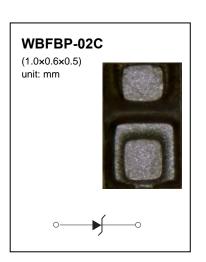
Transient Voltage Suppressors for ESD Protection

DESCRIPTION

The SESDU5V0WB is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

FEATURES

- Stand-off Voltage: 5 V
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 12 kV) Per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- These are Pb-Free Devices
- Pb-Free package is available
 RoHS product for packing code suffix "G"
 Halogen free product for packing code suffix "H"



Maximum Ratings @Ta=25℃

	Symbol	Limit	Unit	
IEC61000-4-2(ESD)	Air/ Contact		±15	kV
ESD voltage	Per Human Body Model		12	kV
	Per Machine Model		400	V
Total power dissipation on FF	\mathbf{P}_{D}	100	mW	
Thermal resistance junction-	$R_{\Theta JA}$	···1250 ·····	℃ /W	
Lead solder temperature - m	TL	260	°C	
Junction and storage temper	$T_{j,} T_{stg}$	-55 ~ +150	℃	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended. Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

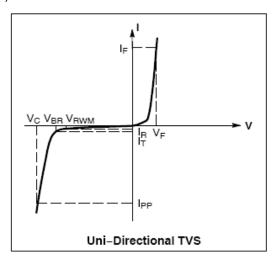
1. $FR-5 = 1.0 \times 0.75 \times 0.62$ in.



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ELECTRICAL CHARACTERISTICS (Ta = 25°C unless otherwise noted)

Symbol	Parameter						
I _{PP}	Maximum Reverse Peak Pulse Current						
Vc	Clamping Voltage @ IPP						
V_{RWM}	Working Peak Reverse Voltage						
I _R	Maximum Reverse Leakage Current @ V _{RWM}						
V_{BR}	Breakdown Voltage @ I _T						
I _T	Test Current						
I _F	Forward Current						
V _F	Forward Voltage @ I _F						
P _{pk}	Peak Power Dissipation						
С	Max. Capacitance @V _R =0 and f =1MHz						



ELECTRICAL CHARACTERISTICS (Ta = 25°C unless otherwise noted)

Device*	Device Marking	V _{RWM} (V)	I _R (μΑ) @ V _{RWM}	V _{BR} (V) @ Ι _τ (Note 2)		I _τ (mA)	MAX I _{PP} (A)	V _с (V) @Мах I _{РР}	C (pF)@ V _R =0V,f=1MHz
		Max	Max	Min	Max	-	-	Max	Тур
SESDU5V0WB	AE	5	1	5.4	9.4	1	1	10	0.5

^{*}Other voltages available upon request.

^{2.} V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.